

RSH110N03TB-VB Datasheet

N-Channel 30-V (D-S) MOSFET

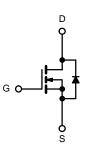
PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)			
30	0.008 at V _{GS} = 10 V	13	6.1 nC			
	0.011 at V _{GS} = 4.5 V	11	0.1110			

FEATURES

- Halogen-free
- Trench Power MOSFET
- Optimized for High-Side Synchronous Rectifier Operation
- 100 % R_g Tested
- 100 % UIS Tested

APPLICATIONS

Notebook CPU Core
High-Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	A - ,			1	
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage		V _{GS}			± 20
	T _C = 25 °C		13		
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	I _D	10]	
$Continuous Drain Current (1) = 150^{\circ} C)$	T _A = 25 °C	D	9 ^{b, c}	1	
	T _A = 70 °C		7 ^{b, c}	A	
Pulsed Drain Current	I _{DM}	45	A		
Continuous Source-Drain Diode Current	T _C = 25 °C	L.	3.7	1	
	T _A = 25 °C	I _S –	2.0 ^{b, c}]	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20	7	
Avalanche Energy L = 0		E _{AS}	21	mJ	
	T _C = 25 °C		4.1		
Movimum Dower Discinction	T _C = 70 °C	PD	2.5	w	
Maximum Power Dissipation	T _A = 25 °C	O 'D	2.2 ^{b, c}		
	T _A = 70 °C		1.3 ^{b, c}	1	
Operating Junction and Storage Temperature Ra	T _J , T _{sta}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	39	55	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	25	29	0/11	

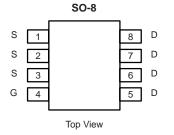
Notes:

a. Base on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s. d. Maximum under Steady State conditions is 85 °C/W.







SPECIFICATIONS $T_J = 25 \text{ °C}$,			Min	Tree	Max	l lm it
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	V	<u> </u>	20			
Drain-Source Breakdown Voltage V _{DS} Temperature Coefficient	V _{DS}	$V_{GS} = 0 V, I_{D} = 250 \mu A$	30	00		V
50	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		26		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	N/ N/ 1 050 A		- 6		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1.0		3.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
	200	V_{DS} = 30 V, V_{GS} = 0 V, T_{J} = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	20			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		0.008		Ω
Dialit-Source Off-State Resistance	· •DS(on)	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 9 \text{ A}$		0.011		52
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		50		S
Dynamic ^b						
Input Capacitance	C _{iss}			800		pF
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		165		
Reverse Transfer Capacitance	C _{rss}			73		
Total Gate Charge	Qg	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		15	23	
				6.8	10.2	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 5 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		2.5		
Gate-Drain Charge	Q _{gd}			2.3		
Gate Resistance	R _g	f = 1 MHz	0.36	1.8	3.6	Ω
Turn-On Delay Time	t _{d(on)}			16	23	_
Rise Time	t _r	V_{DD} = 15 V, R ₁ = 1.4 Ω		12	16	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 4.5 \text{ V}, \text{ R}_g = 1 \Omega$		16	22	
Fall Time	t _f	-		10	18	
Turn-On Delay Time	t _{d(on)}			8	16	ns
Rise Time	t _r	V_{DD} = 15 V, R_{L} = 1.4 Ω		10	20	-
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 10 \text{ V}, \text{R}_g = 1 \Omega$		16	22	
Fall Time	t _f	Ŭ		8	15	
Drain-Source Body Diode Characterist				1	I	1
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			10	
Pulse Diode Forward Current ^a	I _{SM}			1	50	A
Body Diode Voltage	V _{SD}	I _S = 9 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	~		15	30	ns
Body Diode Reverse Recovery Charge	Q _{rr}			6	12	nC
Reverse Recovery Fall Time	t _a	$I_F = 9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^\circ\text{C}$		8		
Reverse Recovery Rise Time	t _b			7		ns

Notes:

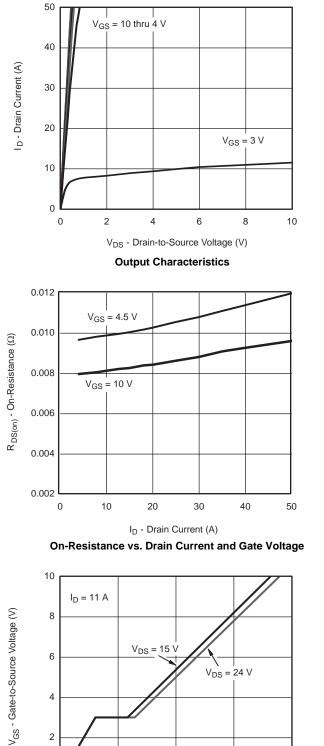
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

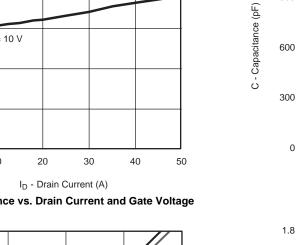
b. Guaranteed by design, not subject to production testing.

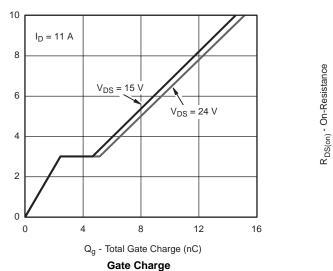
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

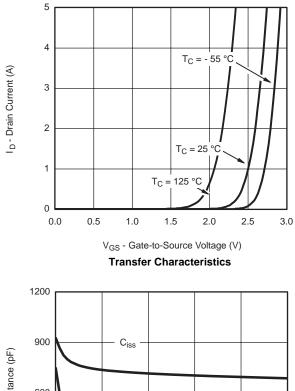


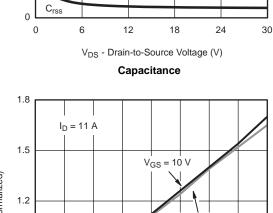
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



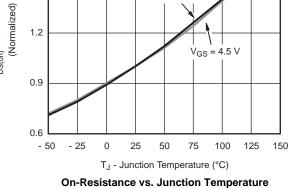








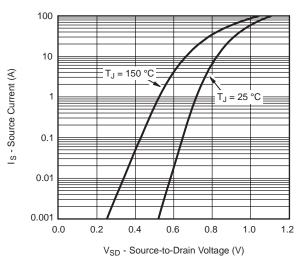
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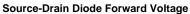


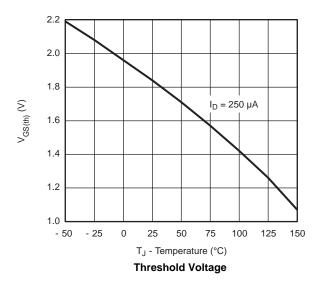
服务热线:400-655-8788

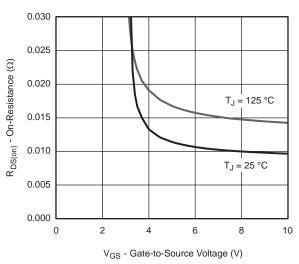


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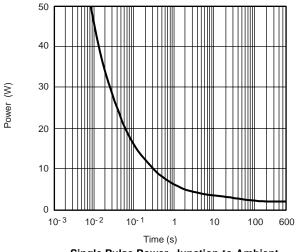




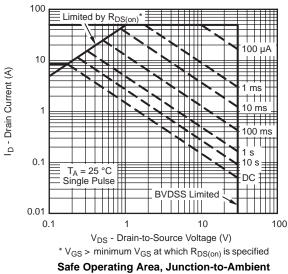




On-Resistance vs. Gate-to-Source Voltage

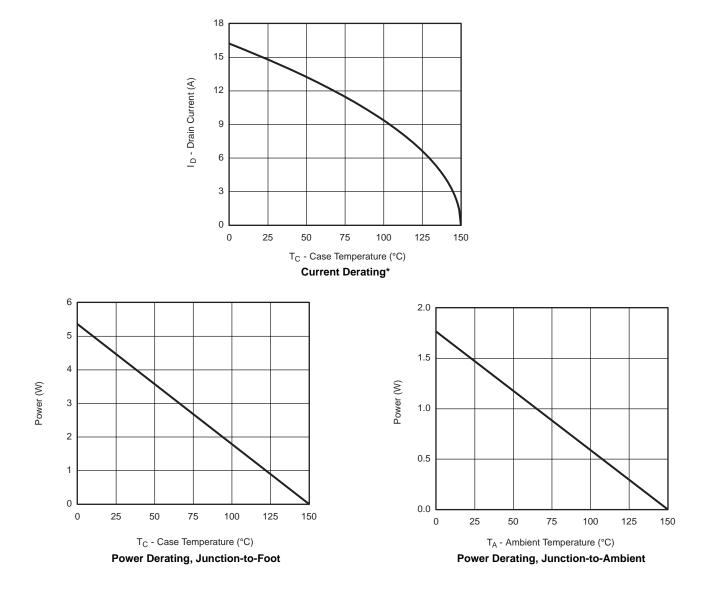






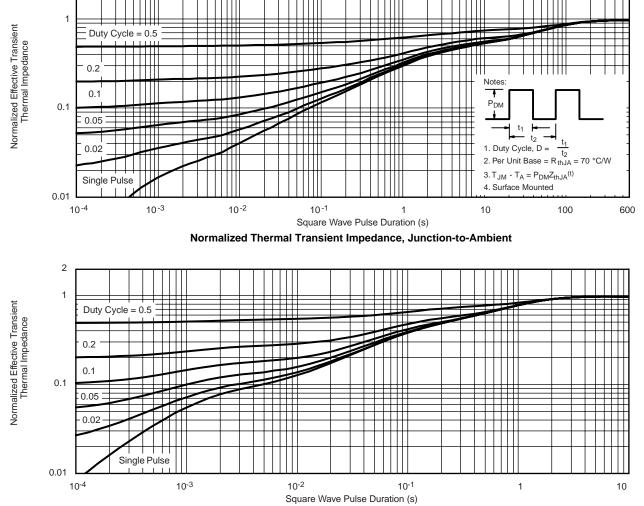


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

2



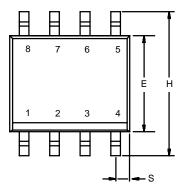
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

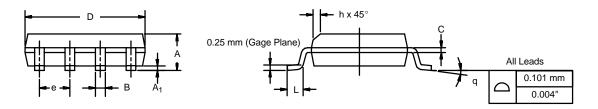
Normalized Thermal Transient Impedance, Junction-to-Foot

<u>VBsemi</u> www.VBsemi.com



SOIC (NARROW): 8-LEAD

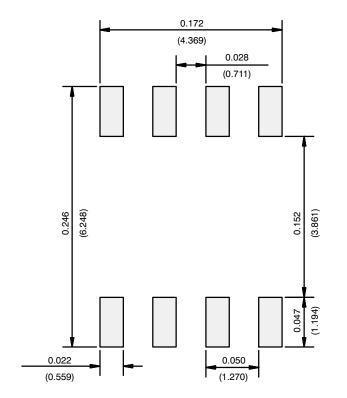




	MILLIMETERS		INC	HES	
DIM	Min	Мах	Min	Max	
A	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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